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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f205rgt6v

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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1 Introduction

This datasheet provides the description of the STM32F205xx and STM32F207xx lines of microcontrollers. For more details on the whole STMicroelectronics STM32 family, please refer to *Section 2.1: Full compatibility throughout the family*.

The STM32F205xx and STM32F207xx datasheet should be read in conjunction with the STM32F20x/STM32F21x reference manual. They will be referred to as STM32F20x devices throughout the document.

For information on programming, erasing and protection of the internal Flash memory, please refer to the STM32F20x/STM32F21x Flash programming manual (PM0059).

The reference and Flash programming manuals are both available from the STMicroelectronics website *www.st.com*.

For information on the Cortex[®]-M3 core please refer to the Cortex[®]-M3 Technical Reference Manual, available from the *www.arm.com* website.



2.1 Full compatibility throughout the family

The STM32F205xx and STM32F207xx constitute the STM32F20x family whose members are fully pin-to-pin, software and feature compatible, allowing the user to try different memory densities and peripherals for a greater degree of freedom during the development cycle.

The STM32F205xx and STM32F207xx devices maintain a close compatibility with the whole STM32F10xxx family. All functional pins are pin-to-pin compatible. The STM32F205xx and STM32F207xx, however, are not drop-in replacements for the STM32F10xxx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xxx to the STM32F20x family remains simple as only a few pins are impacted.

Figure 1, *Figure 2* and *Figure 3* provide compatible board designs between the STM32F20x and the STM32F10xxx family.



Figure 1. Compatible board design between STM32F10xx and STM32F2xx for LQFP64 package





Figure 4. STM32F20x block diagram

1. The timers connected to APB2 are clocked from TIMxCLK up to 120 MHz, while the timers connected to APB1 are clocked from TIMxCLK up to 60 MHz.

2. The camera interface and Ethernet are available only in STM32F207xx devices.



3 Functional overview

3.1 **ARM[®] Cortex[®]-M3 core with embedded Flash and SRAM**

The ARM[®] Cortex[®]-M3 processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM[®] Cortex[®]-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

With its embedded $\text{ARM}^{\text{®}}$ core, the STM32F20x family is compatible with all $\text{ARM}^{\text{®}}$ tools and software.

Figure 4 shows the general block diagram of the STM32F20x family.

3.2 Adaptive real-time memory accelerator (ART Accelerator[™])

The ART Accelerator[™] is a memory accelerator which is optimized for STM32 industrystandard ARM[®] Cortex[®]-M3 processors. It balances the inherent performance advantage of the ARM[®] Cortex[®]-M3 over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher operating frequencies.

To release the processor full 150 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache which increases program execution speed from the 128-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 120 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.



The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see Section 3.18: Low-power modes).

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or the V_{BAT} pin.

3.18 Low-power modes

The STM32F20x family supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

Stop mode

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from the Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup.

• Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped when the device enters the Stop or Standby mode.

3.19 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery or an external supercapacitor.

 V_{BAT} operation is activated when V_{DD} is not present.

The VBAT pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT} , external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When using WLCSP64+2 package, if IRROFF pin is connected to V_{DD} , the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD} .



3.37 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

3.38 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F20x through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.



Figure 16. Memory map





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6.3.5 Embedded reset and power control block characteristics

The parameters given in *Table 19* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	V
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	V
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	V
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	V
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	V
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	V
V _{PVD}	Programmable voltage detector level selection	PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	V
112		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	V
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	V
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	V
		PLS[2:0]=101 (falling edge)	2.65	2.84	3.02	V
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	V
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	V
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	V
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	V
V _{PVDhyst} ⁽¹⁾	PVD hysteresis	-	-	100	-	mV
	Power-on/power-down	Falling edge	1.60	1.68	1.76	V
POR/PDR	reset threshold	Rising edge	1.64	1.72	1.80	V
V _{PDRhyst} ⁽¹⁾	PDR hysteresis	-	-	40	-	mV
Vecer	Brownout level 1	Falling edge	2.13	2.19	2.24	V
VBOR1	threshold	Rising edge	2.23	2.29	2.33	V





Figure 35. ACC_{LSI} versus temperature

6.3.10 PLL characteristics

The parameters given in *Table 34* and *Table 35* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
f _{PLL_IN}	PLL input clock ⁽¹⁾	-	0.95 ⁽²⁾	1	2.10 ⁽²⁾	MHz	
f _{PLL_OUT}	PLL multiplier output clock	-	24	-	120	MHz	
f _{PLL48_OUT}	48 MHz PLL multiplier output clock	-	-	-	48	MHz	
f _{VCO_OUT}	PLL VCO output	-	192	-	432	MHz	
t _{LOCK}	PLL lock time	VCO freq = 192 MHz	75	-	200	μs	
		VCO freq = 432 MHz	100	-	300		

Table 34. Main PLL characteristics



Electrical characteristics

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
			C_L = 50 pF, V_{DD} > 2.70 V)V 25				
	f	Marian (2)	C _L = 50 pF, V _{DD >} 1.8 V	-	-	12.5		
	^I max(IO)out		C _L = 10 pF, V _{DD >} 2.70 V	-	-	50 ⁽³⁾		
04			C _L = 10 pF, V _{DD >} 1.8 V	-	-	20		
01			C _L = 50 pF, V _{DD} >2.7 V	-	-	10		
	t _{f(IO)out} /	Output high to low level fall	C _L = 50 pF, V _{DD >} 1.8 V	-	-	20	20	
	t _{r(IO)out}	level rise time	C _L = 10 pF, V _{DD >} 2.70 V	-	-	6	115	
			C _L = 10 pF, V _{DD >} 1.8 V	-	-	10		
			C _L = 40 pF, V _{DD >} 2.70 V	-	-	25		
	f _{max(IO)out}	Maximum frequency ⁽²⁾	C _L = 40 pF, V _{DD >} 1.8 V	-	-	20	MHz	
			C _L = 10 pF, V _{DD >} 2.70 V	-	-	100 ⁽³⁾		
			C _L = 10 pF, V _{DD >} 1.8 V	-	-	50 ⁽³⁾		
10	t _{f(IO)out} / t _{r(IO)out}		C _L = 40 pF, V _{DD >} 2.70 V	-	-	6		
		Output high to low level fall time and output low to high level rise time	C _L = 40 pF, V _{DD >} 1.8 V	-	-	10	ns	
			C _L = 10 pF, V _{DD >} 2.70 V	-	-	4		
			C _L = 10 pF, V _{DD >} 1.8 V	-	-3	6		
			C _L = 30 pF, V _{DD >} 2.70 V	-	-	100 ⁽³⁾		
	£	Maximum fragman (2)	C _L = 30 pF, V _{DD >} 1.8 V	-	-	50 ⁽³⁾	MHz	
	Tmax(IO)out	Maximum frequency ⁽²⁾	C _L = 10 pF, V _{DD >} 2.70 V	-	-	120 ⁽³⁾		
11			C _L = 10 pF, V _{DD >} 1.8 V	-	-	100 ⁽³⁾		
11			C _L = 30 pF, V _{DD >} 2.70 V	-	-	4		
	t _{f(IO)out} /	Output high to low level fall	C _L = 30 pF, V _{DD >} 1.8 V	-	-	6	ns	
	t _{r(IO)out}	time and output low to high level rise time	C _L = 10 pF, V _{DD >} 2.70 V	-	-	2.5		
			C _L = 10 pF, V _{DD >} 1.8 V	-	-	4		
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-	-	ns	

Table 48. I/O AC characteristics ⁽¹⁾ ((continued)
---	-------------

 The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F20/21xxx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.

2. The maximum frequency is defined in *Figure 39*.

3. For maximum frequencies above 50 MHz and V_{DD} above 2.4 V, the compensation cell should be used.



Symbol	Parameter	Conditions	Min	Мах	Unit
t _{res(TIM)}		AHB/APB2	1	-	t _{TIMxCLK}
	Timer resolution time	from 1, f _{TIMxCLK} = 120 MHz	8.3	-	ns
		AHB/APB2	1	-	t _{TIMxCLK}
		f _{TIMxCLK} = 60 MHz	16.7	-	ns
feve	Timer external clock		0	f _{TIMxCLK} /2	MHz
'EXT	frequency on CH1 to CH4		0	60	MHz
Res _{TIM}	Timer resolution		-	16	bit
t _{COUNTER}	16-bit counter clock period	$T_{TIMxCLK} = 120 \text{ MHz}$	1	65536	t _{TIMxCLK}
	selected	AF 62 - 00 MHZ	0.0083	546	μs
t _{MAX_COUNT}	Maximum possible count		-	65536 × 65536	t _{TIMxCLK}
			-	35.79	S

 Table 51. Characteristics of TIMx connected to the APB2 domain⁽¹⁾

1. TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

6.3.19 Communications interfaces

I²C interface characteristics

STM32F205xx and STM32F207xx I^2 C interface meets the requirements of the standard I^2 C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in *Table 52*. Refer also to *Section 6.3.16*: I/O port characteristics for more details on the input/output alternate function characteristics (SDA and SCL).



Symbol	Parameter	Min	Тур	Max	Unit	Comments
DAC_OUT min ⁽²⁾	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion
DAC_OUT max ⁽²⁾	Higher DAC_OUT voltage with buffer OFF	-	-	V _{REF+} – 1LSB	V	of the DAC.
. (4)	DAC DC V _{REF} current consumption in quiescent mode (Standby mode)	-	170	240		With no load, worst code (0x800) at V _{REF+} = 3.6 V in terms of DC consumption on the inputs
VREF+`´		-	50	75	μΑ	With no load, worst code (0xF1C) at V _{REF+} = 3.6 V in terms of DC consumption on the inputs
	DAC DC V _{DDA} current	-	280	380	μA	With no load, middle code (0x800) on the inputs
I _{DDA} ⁽⁴⁾	consumption in quiescent mode ⁽³⁾	-	475	625	μA	With no load, worst code (0xF1C) at V _{REF+} = 3.6 V in terms of DC consumption on the inputs
DNL ⁽⁴⁾	Differential non linearity Difference between two	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration.
	consecutive code-1LSB)	-	-	±2	LSB	Given for the DAC in 12-bit configuration.
	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±1	LSB	Given for the DAC in 10-bit configuration.
INL ⁽⁴⁾		-	-	±4	LSB	Given for the DAC in 12-bit configuration.
	Offset error	-	-	±10	mV	-
Offset ⁽⁴⁾	(difference between measured value at Code	-	-	±3	LSB	Given for the DAC in 10-bit at V _{REF+} = 3.6 V
	(0x800) and the ideal value = V _{REF+} /2)	-	-	±12	LSB	Given for the DAC in 12-bit at V _{REF+} = 3.6 V
Gain error ⁽⁴⁾	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
t _{SETTLING} ⁽⁴⁾	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±4LSB	-	3	6	μs	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$
THD ⁽⁴⁾	Total Harmonic Distortion Buffer ON	-	-	-	dB	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$

Table 68. DAC characteristics (continued)



Symbol	Parameter	Min	Max	Unit
t _{d(CLKL-NWEL)}	FSMC_CLK low to FSMC_NWE low	-	1	ns
t _{d(CLKL-NWEH)}	FSMC_CLK low to FSMC_NWE high	0	-	ns
t _{d(CLKL-ADIV)}	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
t _{d(CLKL-DATA})	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	2	ns
t _{d(CLKL-NBLH)}	FSMC_CLK low to FSMC_NBL high	0.5	-	ns

Table 77. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾ (continued)

1. C_L = 30 pF.

2. Guaranteed by characterization results, not tested in production.



Figure 63. Synchronous non-multiplexed NOR/PSRAM read timings

Table 78. Synchronous non-multiplexed NOR/PSRAM read	timinas ⁽¹⁾⁽²⁾
Table 70. Oynemonous non-maniplexed North Ortam read	unnigs

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	FSMC_CLK period	2T _{HCLK}	-	ns
t _{d(CLKL-NExL)}	FSMC_CLK low to FSMC_NEx low (x=02)	-	0	ns
t _{d(CLKL-NExH)}	FSMC_CLK low to FSMC_NEx high (x= 02)	1	-	ns
t _{d(CLKL-NADVL)}	FSMC_CLK low to FSMC_NADV low	-	2.5	ns



Symbol	Parameter	Min	Max	Unit
t _{d(CLKL-NADVH)}	FSMC_CLK low to FSMC_NADV high	4	-	ns
t _{d(CLKL-AV)}	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	ns
t _{d(CLKL-AIV)}	FSMC_CLK low to FSMC_Ax invalid (x=1625)	3	-	ns
t _{d(CLKH-NOEL)}	IOEL) FSMC_CLK high to FSMC_NOE low		1	ns
t _{d(CLKL-NOEH)}	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
t _{su(DV-CLKH)}	LKH) FSMC_D[15:0] valid data before FSMC_CLK high		-	ns
t _{h(CLKH-DV)}	FSMC_D[15:0] valid data after FSMC_CLK high	0	-	ns

Table 78. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾ (continued)

1. C_L = 30 pF.

2. Guaranteed by characterization results, not tested in production.



Figure 64. Synchronous non-multiplexed PSRAM write timings

Table 79. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	FSMC_CLK period	2T _{HCLK} - 1	-	ns
t _{d(CLKL-NExL)}	FSMC_CLK low to FSMC_NEx low (x=02)	-	1	ns
t _{d(CLKL-NExH)}	FSMC_CLK low to FSMC_NEx high (x= 02)	1	-	ns





Figure 85. LQFP144 - 144-pin,20 x 20 mm low-profile quad flat package recommended footprint

1. Dimensions are expressed in millimeters.



8 Part numbering

Table 96. Ordering information	tion scheme					
Example:	STM32 F	205	R	E	Т 6	Vxxx
Device family						
STM32 = APM based 32 bit microcontroller						
STMSZ – ARM-based Sz-bit microcontroller						
Product type						
F = general-purpose						
Device subfamily						
205 = STM32F20x, connectivity						
207= STM32F20x, connectivity, camera interface,						
Ethernet						
Pin count						
R = 64 pins or 66 pins ⁽¹⁾						
V = 100 pins						
Z = 144 pins						
I = 176 pins						
Flash memory size						
B = 128 Kbytes of Flash memory						
C = 256 Kbytes of Flash memory						
E = 512 Kbytes of Flash memory						
F = 768 Kbytes of Flash memory						
G = 1024 Kbytes of Flash memory						
Package						
T = LQFP						
H = UFBGA						
Y = WLCSP						
Temperature range						
6 = Industrial temperature range, -40 to 85 °C.						
7 = Industrial temperature range, –40 to 105 °C.						
Software option						
Internal code or Blank						
Options						
epitone						

xxx = programmed parts TR = tape and reel

1. The 66 pins is available on WLCSP package only.

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.



9 Revision history

Data	Povision	Changes			
Dale	Revision	Changes			
05-Jun-2009	1	Initial release.			
09-Oct-2009	2	 Document status promoted from Target specification to Preliminary data. In <i>Table 8: STM32F20x pin and ball definitions</i>: Note 4 updated V_{DD_SA} and V_{DD_3} pins inverted (<i>Figure 12: STM32F20x LQFP100 pinout, Figure 13: STM32F20x LQFP144 pinout</i> and <i>Figure 14: STM32F20x LQFP176 pinout</i> corrected accordingly). Section : In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark. changed to LQFP with no exposed pad. 			
01-Feb-2010	3	LFBGA144 package removed. STM32F203xx part numbers removed. Part numbers with 128 and 256 Kbyte Flash densities added. Encryption features removed. PC13-TAMPER-RTC renamed to PC13-RTC_AF1 and PI8-TAMPER- RTC renamed to PI8-RTC_AF2.			
13-Jul-2010	4	 Renamed high-speed SRAM, system SRAM. Removed combination: 128 KBytes Flash memory in LQFP144. Added UFBGA176 package. Added note 1 related to LQFP176 package in <i>Table 2, Figure 14</i>, and <i>Table 96</i>. Added information on ART accelerator and audio PLL (PLLI2S). Added <i>Table 6: USART feature comparison</i>. Several updates on <i>Table 8: STM32F20x pin and ball definitions</i> and <i>Table 10: Alternate function mapping</i>. ADC, DAC, oscillator, RTC_AF, WKUP and VBUS signals removed from alternate functions and moved to the "other functions" column in <i>Table 8: STM32F20x pin and ball definitions</i>. TRACESWO added in <i>Figure 4: STM32F20x block diagram, Table 8: STM32F20x pin and ball definition</i> mapping. XTAL oscillator frequency updated on cover page, in <i>Figure 4: STM32F20x block diagram</i> and in <i>Section 3.11: External interrupt/event controller (EXTI)</i>. Updated list of peripherals used for boot mode in <i>Section 3.13: Boot modes</i>. Added Regulator bypass mode in <i>Section 3.16: Voltage regulator</i>, and <i>Section 6.3.4: Operating conditions at power-up / power-down (regulator OFF)</i>. Updated Section 3.17: <i>Real-time clock (RTC), backup SRAM and backup registers</i>. Added Note Note: in <i>Section 3.23: Serial peripheral interface (SPI)</i>. 			

Table 97.	Document	revision	history
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Date	Revision	Changes		
		Changed minimum supply voltage from 1.65 to 1.8 V.		
		Updated number of AHB buses in <i>Section 2: Description</i> and <i>Section 3.12: Clocks and startup</i> .		
		Removed Figure 4. Compatible board design between STM32F10xx and STM32F2xx for LQFP176 package.		
		Updated Note 2 below Figure 4: STM32F20x block diagram.		
		Changed System memory to System memory + OTP in <i>Figure 16: Memory map</i> .		
		Added Note 1 below Table 16: VCAP1/VCAP2 operating conditions.		
		Updated V _{DDA} and V _{REF+} decouping capacitor in <i>Figure 19: Power supply scheme</i> and updated <i>Note 3</i> .		
		Changed simplex mode into half-duplex mode in <i>Section 3.24: Inter-integrated sound (I2S)</i> .		
		Replaced DAC1_OUT and DAC2_OUT by DAC_OUT1 and DAC_OUT2, respectively.Changed TIM2_CH1/TIM2_ETR into TIM2_CH1_ETR for PA0 and PA5 in <i>Table 10: Alternate function</i>		
		Updated note applying to I _{DD} (external clock and all peripheral disabled) in Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled). Updated Note 3 below Table 22: Typical and		
		maximum current consumption in Sleep mode.		
29-Oct-2012	10	Removed f _{HSE_ext} typical value in <i>Table 28: High-speed external user clock characteristics</i> .		
		Updated master I2S clock jitter conditions and vlaues in <i>Table 35: PLLI2S (audio PLL) characteristics</i> .		
		Updated equations in Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics.		
		Swapped TTL and CMOS port conditions for V _{OL} and V _{OH} in <i>Table 47: Output voltage characteristics</i> .		
		Updated $V_{IL(NRST)}$ and $V_{IH(NRST)}$ in <i>Table 49: NRST pin characteristics</i> . Updated <i>Table 54: SPI characteristics</i> and <i>Table 55: I2S characteristics</i> . Removed note 1 related to measurement points below <i>Figure 43: SPI timing diagram - slave mode and CPHA = 1, Figure 44: SPI timing diagram - master mode</i> , and <i>Figure 45: I2S slave timing diagram (Philips protocol)(1)</i> .		
		Updated t _{HC} in <i>Table 61: ULPI timing</i> .		
		Updated Figure 49: Ethernet SMI timing diagram, Table 63: Dynamics characteristics: Ethernet MAC signals for SMI and Table 65: Dynamics characteristics: Ethernet MAC signals for MII.		
		Update f _{TRIG} in Table 66: ADC characteristics.		
		Updated I _{DDA} description in <i>Table 68: DAC characteristics</i> .		
		Updated note below <i>Figure 54: Power supply and reference decoupling</i> (<i>VREF+ not connected to VDDA</i>) and <i>Figure 55: Power supply and reference decoupling</i> (<i>VREF+ connected to VDDA</i>).		

Table 97	Document	revision	history	(continued)
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